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Form PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

LIST OF ART CITED BY APPLICANT
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ATTY. DOCKET NO.	SERIAL NO.
M122-2362	10/625,068
APPLICANT: Arup Bhattacharyya	
FILING DATE: July 22, 2003	GROUP: 2824

U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
CDW	AA	6,593,624 B2	07/03	Walker	257	344	
CDW	AB	6,204,608 B1	03/01	Song et al.	315	169.3	
	AC						
	AD						
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	AF						
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	AH						
	AI						
	AJ						
	AK						
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FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation Yes	Translation No
	AM							
	AN							
	AO							
	AP							
	AQ							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

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EXAMINER: Christian Wilson

DATE CONSIDERED: 11/4/04

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ATTY. DOCKET NO.	SERIAL NO.
MI22-2362	10/625,068
APPLICANT: Arup Bhattacharyya	
FILING DATE: July 22, 2003	GROUP 2824

U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
CDW	AA	US 2003/ 0013305 A1	Pub. 01/03	Sugii et al.	438	689	06/07/02
CDW	AB	US 2002/ 0045312 A1	Pub. 04/02	Zheng et al.	438	253	07/19/01
CDW	AC	US 2002/ 0014625 A1	Pub. 02/02	Asami et al.	257	57	08/01/01
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FOREIGN PATENT DOCUMENTS

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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

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EXAMINER: Chris C. Bo | DATE CONSIDERED: 11/4/04

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EV317136323

Form PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. M122-2362	SERIAL NO 10/625068
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)		APPLICANT Arup Bhattacharyya	
		PRIORITY FILING DATE September 12, 2002	GROUP 2824

			OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)
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	AK		Kesan, V. et al., "High Performance 0.25μm p-MOSFETs with Silicon- Germanium Channels for 300K and 77K Operation", IEDM Tech. Digest, 1991, pp. 25-28.
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Christian Wilson	11/4/04

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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)	APPLICANT Arup Bhattacharyya	
	PRIORITY FILING DATE September 12, 2002	GROUP 2824

			OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)
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	AP		Ernst, T. et al., "Fabrication of a Novel Strained SiGe:C-channel Planar 55 nm nMOSFET for High-Performance CMOS", 2002 Sympos. on VLSI Tech. Digest of Technical Papers, pp. 92-93.
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EXAMINER Christian Wilson	DATE CONSIDERED 11/4/04

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			OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)
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	AY		Tezuka, T. et al., "High-Performance Strained Si-on-Insulator MOSFETs by Novel Fabrication Processes Utilizing Ge-Condensation Technique", 2002 VLSI Tech. Digest of Technical Papers, pp. 96-97.
	AZ		Takagi, S., "Strained-Si- and SiGe-on-Insulator (Strained SOI and SGOI) MOSFETs for High Performance/Low Power CMOS Application", DRC Conf. Digest, 2002, pp. 37-40.
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	BB		Markoff, J., "I.B.M. Circuits are Now Faster and Reduce Use of Power", The New York Times, Feb. 25, 2002, reprinted 3/20/02 from http://story.news.yahoo.com/ news?tmpl=story&u=/nyt/20020225/..., 1 pg.
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	BF		Myers, S.M. et al., "Deuterium Interactions in Oxygen-Implanted Copper", J. Appl. Phys., Vol. 65(1), Jan. 1, 1989, p. 311-321.
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	BH		Lu, N.C.C. et al., "A Buried-Trench DRAM Cell Using a Self-Aligned Epitaxy Over Trench Technology", IEDM Tech. Digest, 1988, pp. 588-591.
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EXAMINER Christia Wilson	DATE CONSIDERED 11/4/04

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Form PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MI22-2362	SERIAL NO 10/625068
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)		APPLICANT Arup Bhattacharyya	
		PRIORITY FILING DATE September 12, 2002	GROUP 2824

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)			
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			nm Applications", 2001 IEEE Internatl. SOI Conf. 10/01, pp. 45-46.
	BK		
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EXAMINER Christian Carlson	DATE CONSIDERED 11/4/04

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